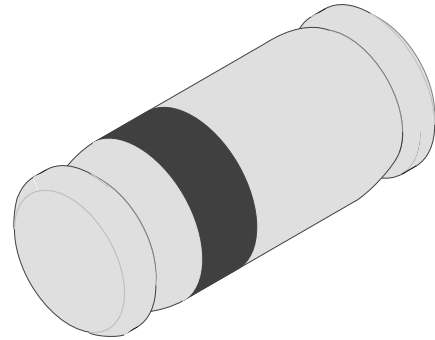


Switching Diode

Features

- Silicon Epitaxial Planar Diodes



94 9371

Applications

General purposes

Order Instruction

| Type | Type Differentiation | Ordering Code | Remarks |
|--------|--------------------------|---------------|---------------|
| BAV100 | $V_{RRM} = 60\text{ V}$ | BAV100-GS08 | Tape and Reel |
| BAV101 | $V_{RRM} = 120\text{ V}$ | BAV101-GS08 | Tape and Reel |
| BAV102 | $V_{RRM} = 200\text{ V}$ | BAV102-GS08 | Tape and Reel |
| BAV103 | $V_{RRM} = 250\text{ V}$ | BAV103 -GS08 | Tape and Reel |

Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

| Parameter | Test Conditions | Type | Symbol | Value | Unit |
|---------------------------------|------------------|--------|-----------|------------|------------------|
| Repetitive peak reverse voltage | | BAV100 | V_{RRM} | 60 | V |
| | | BAV101 | V_{RRM} | 120 | V |
| | | BAV102 | V_{RRM} | 200 | V |
| | | BAV103 | V_{RRM} | 250 | V |
| Reverse voltage | | BAV100 | V_R | 50 | V |
| | | BAV101 | V_R | 100 | V |
| | | BAV102 | V_R | 150 | V |
| | | BAV103 | V_R | 200 | V |
| Peak forward surge current | $t_p=1\text{ s}$ | | I_{FSM} | 1 | A |
| Repetitive peak forward current | | | I_{FRM} | 625 | mA |
| Forward current | | | I_F | 250 | mA |
| Power dissipation | | | P_V | 500 | mW |
| Junction temperature | | | T_j | 175 | $^\circ\text{C}$ |
| Storage temperature range | | | T_{stg} | -65...+175 | $^\circ\text{C}$ |

Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Value | Unit |
|------------------|--------------------------------|------------|-------|------|
| Junction lead | | R_{thJL} | 350 | K/W |
| Junction ambient | on PC board 50 mmx50 mmx1.6 mm | R_{thJA} | 500 | K/W |

Electrical Characteristics

$T_j = 25^\circ\text{C}$

| Parameter | Test Conditions | Type | Symbol | Min | Typ | Max | Unit |
|---------------------------------|---|--------|------------|-----|-----|-----|---------------|
| Forward voltage | $I_F=100\text{mA}$ | | V_F | | | 1 | V |
| Reverse current | $V_R=50\text{ V}$ | BAV100 | I_R | | | 100 | nA |
| | $V_R=100\text{ V}$ | BAV101 | I_R | | | 100 | nA |
| | $V_R=150\text{ V}$ | BAV102 | I_R | | | 100 | nA |
| | $V_R=200\text{ V}$ | BAV103 | I_R | | | 100 | nA |
| | $T_j=100^\circ\text{C}$, $V_R=50\text{ V}$ | BAV100 | I_R | | | 15 | μA |
| | $T_j=100^\circ\text{C}$, $V_R=100\text{ V}$ | BAV101 | I_R | | | 15 | μA |
| | $T_j=100^\circ\text{C}$, $V_R=150\text{ V}$ | BAV102 | I_R | | | 15 | μA |
| | $T_j=100^\circ\text{C}$, $V_R=200\text{ V}$ | BAV103 | I_R | | | 15 | μA |
| Breakdown voltage | $I_R=100\mu\text{A}$, $t_p/T=0.01$, $t_p=0.3\text{ms}$ | BAV100 | $V_{(BR)}$ | 60 | | | V |
| | | BAV101 | $V_{(BR)}$ | 120 | | | V |
| | | BAV102 | $V_{(BR)}$ | 200 | | | V |
| | | BAV103 | $V_{(BR)}$ | 250 | | | V |
| Diode capacitance | $V_R=0$, $f=1\text{MHz}$ | | C_D | | 1.5 | | pF |
| Differential forward resistance | $I_F=10\text{mA}$ | | r_f | | 5 | | Ω |
| Reverse recovery time | $I_F=I_R=30\text{mA}$, $i_R=3\text{mA}$, $R_L=100\Omega$ | | t_{rr} | | | 50 | ns |

Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

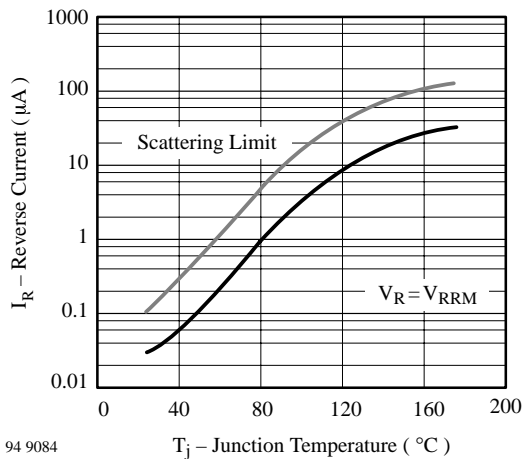


Figure 1. Reverse Current vs. Junction Temperature

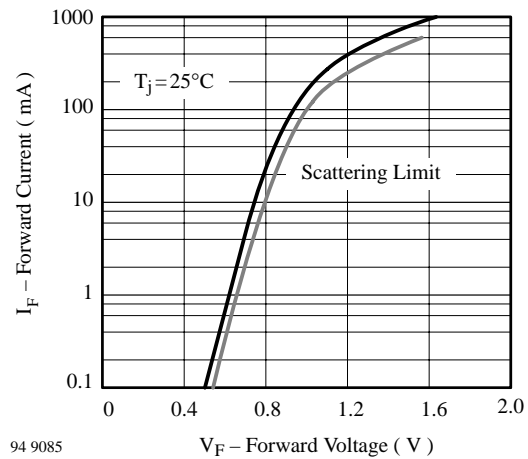


Figure 2. Forward Current vs. Forward Voltage

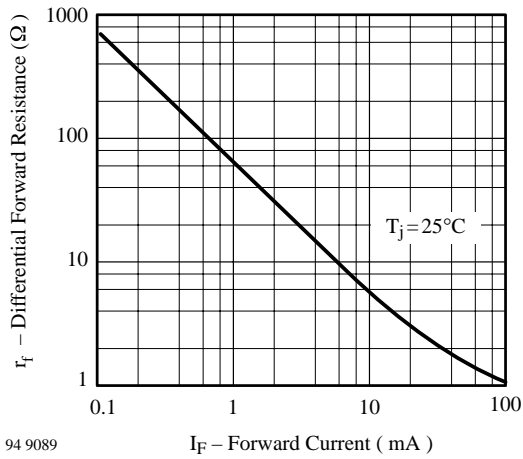
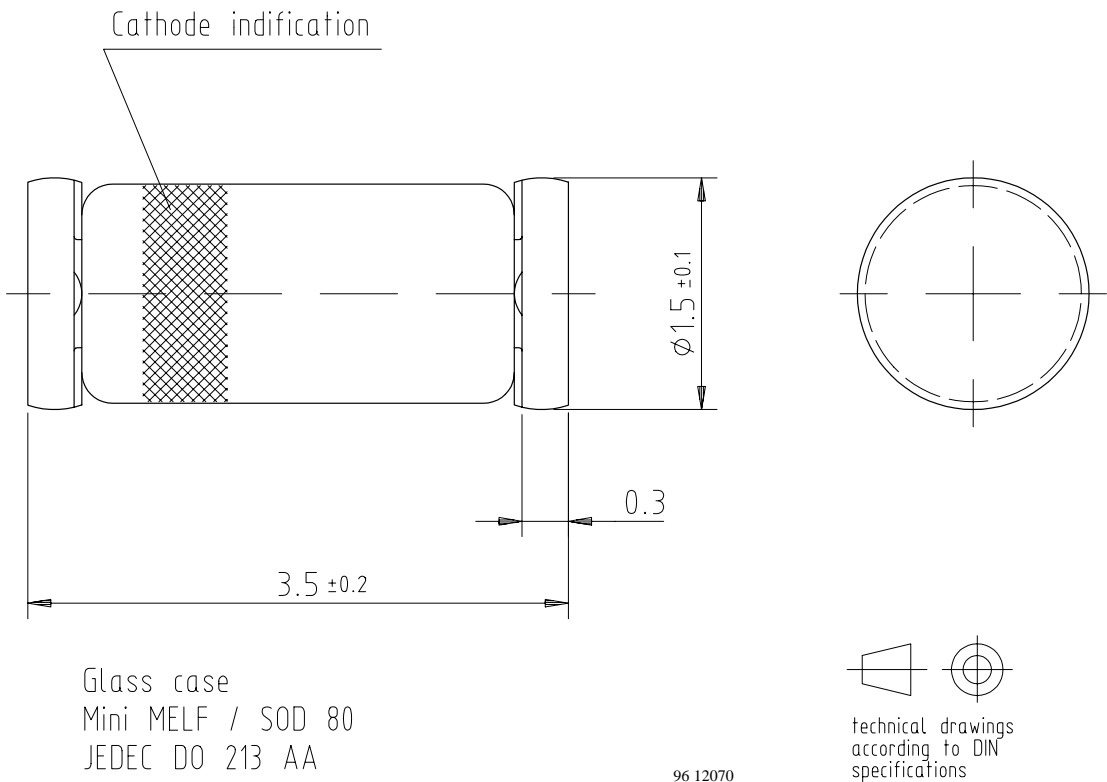


Figure 3. Differential Forward Resistance vs. Forward Current

Dimensions in mm



96 12070

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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